L Number	Hits	Search Text	DB	Time stamp
1	66	438/288.ccls.	USPAT	2004/03/11 10:47
2	906	438/585.ccls. 438/591.ccls.	USPAT	2004/03/11 10:47
3	963	(438/585.ccls. 438/591.ccls.) 438/288.ccls.	USPAT	2004/03/11 10:47
–	20394	gate adj2 insulating	USPAT; EPO; JPO	2002/10/29 16:07
–	19039	thin adj2 oxide) (ultrathin adj2 oxide	USPAT; EPO; JPO	2002/10/29 16:07
–	1124	(gate adj2 insulating) and (thin adj2 oxide) (ultrathin adj2 oxide) and polysilicon	USPAT; EPO; JPO	2002/10/29 16:08
–	188199	hydrogen and oxygen	USPAT; EPO; JPO	2002/10/29 16:08
–	227	(hydrogen and oxygen) and ((gate adj2 insulating) and (thin adj2 oxide) (ultrathin adj2 oxide) and polysilicon)	USPAT; EPO; JPO	2002/10/29 16:08
–	101606	hydrogen same oxygen	USPAT; EPO; JPO	2002/10/29 16:09
–	122	(hydrogen same oxygen) and ((gate adj2 insulating) and (thin adj2 oxide) (ultrathin adj2 oxide) and polysilicon)	USPAT; EPO; JPO	2002/10/29 16:13
–	80371	hydrogen with oxygen	USPAT; EPO; JPO	2002/10/29 16:14
–	88	(hydrogen with oxygen) and ((gate adj2 insulating) and (thin adj2 oxide) (ultrathin adj2 oxide) and polysilicon)	USPAT; EPO; JPO	2002/10/30 10:11
–	1	(hydrogen with oxygen) and ((gate adj2 insulating) and (thin adj2 oxide) (ultrathin adj2 oxide) and polysilicon) and ISSG	USPAT; EPO; JPO	2002/10/30 10:16
–	9	ISSG "in situ steam generation"	USPAT; EPO; JPO	2004/02/26 13:44
–	8	(ISSG "in situ steam generation") and gate	USPAT; EPO; JPO	2002/10/30 10:31

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–	5957	EEPROM and oxide	USPAT; EPO; JPO	2003/04/27 14:47
–	54	(EEPROM and oxide) and SONOS	USPAT; EPO; JPO	2003/04/27 14:49
–	280	EEPROM and ("form oxide")	USPAT; EPO; JPO	2003/04/27 14:52
–	0	EEPROM and ("form oxide") near (oxygen adj3 hydrogen)	USPAT; EPO; JPO	2003/04/27 14:52
–	1	("form oxide") near (oxygen adj3 hydrogen)	USPAT; EPO; JPO	2003/04/27 14:53
–	184	("wet oxidation" or "steam oxidation") and EEPROM	USPAT; EPO; JPO	2003/04/27 15:00
–	16	(("wet oxidation" or "steam oxidation") and EEPROM) and (ultrathin "ultra thin" "ultra-thin")	USPAT; EPO; JPO	2003/04/27 15:01
–	1694	(((hydrogen or "H.Sub.2") near "3" (oxygen or "O.sub.2")) or (pyrogenic pyrogenically pyrogenical wet steam)) near12 (oxidiz$3 oxidis$3 oxidation anneal$4 RTO) near12 (SiN("Si.sub.3" adj "N.sub.4") Si3N4 nitride)	USPAT; EPO; JPO	2003/04/28 12:36
–	0	((((hydrogen or "H.Sub.2") near "3" (oxygen or "O.sub.2")) or (pyrogenic pyrogenically pyrogenical wet steam)) near12 (oxidiz$3 oxidis$3 oxidation anneal$4 RTO) near12 (SiN("Si.sub.3" adj "N.sub.4") Si3N4 nitride)) and "ultrathin oxide"	USPAT; EPO; JPO	2003/04/28 12:37
–	6	((((hydrogen or "H.Sub.2") near "3" (oxygen or "O.sub.2")) or (pyrogenic pyrogenically pyrogenical wet steam)) near12 (oxidiz$3 oxidis$3 oxidation anneal$4 RTO) near12 (SiN("Si.sub.3" adj "N.sub.4") Si3N4 nitride)) and (ultrathin near3 oxide)	USPAT; EPO; JPO	2003/04/28 12:48
–	26	((((hydrogen or "H.Sub.2") near "3" (oxygen or "O.sub.2")) or (pyrogenic pyrogenically pyrogenical wet steam)) near12 (oxidiz$3 oxidis$3 oxidation anneal$4 RTO) near12 (SiN("Si.sub.3" adj "N.sub.4") Si3N4 nitride)) and gardner.inv.	USPAT; EPO; JPO	2003/04/28 12:55
–	23	reoxidize near6 nitrogen	USPAT; EPO; JPO	2003/04/28 12:56
–	99	((((hydrogen or "H.Sub.2") near "3" (oxygen or "O.sub.2")) or (pyrogenic pyrogenically pyrogenical wet steam)) near12 (oxidiz$3 oxidis$3 oxidation anneal$4 RTO) near12 (SiN("Si.sub.3" adj "N.sub.4") Si3N4 nitride)) and EEPROM	USPAT; EPO; JPO	2003/04/28 13:28
–	2	(RTO "rapid thermal oxidation") near5 minute	USPAT; EPO; JPO	2003/04/28 13:28
–	690	"tunnel oxide".clm.	USPAT; EPO; JPO	2004/02/26 13:45

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